

# Patrick Desjardins

## List of Publications by Year in descending order

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121  
papers

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| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 1  | Longitudinal piezoelectric, elastic, and dielectric properties of rare-earth aluminum nitride alloys determined by density-functional perturbation theory. <i>Physical Review Materials</i> , 2022, 6, .                         | 2.4  | 2         |
| 2  | Impact of applied biaxial stress on the piezoelectric, elastic, and dielectric properties of scandium aluminum nitride alloys determined by density functional perturbation theory. <i>AIP Advances</i> , 2021, 11, .            | 1.3  | 3         |
| 3  | Double-walled carbon nanotube film as the active electrode in an electro-optical modulator for the mid-infrared and terahertz regions. <i>Journal of Applied Physics</i> , 2020, 128, .  | 2.5  | 8         |
| 4  | Ab initio piezoelectric properties of wurtzite ZnO-based alloys: Impact of the c/a cell ratio. <i>Physical Review Materials</i> , 2020, 4, .   | 2.4  | 4         |
| 5  | Alignment of semiconducting graphene nanoribbons on vicinal Ge(001). <i>Nanoscale</i> , 2019, 11, 4864-4875.   | 5.6  | 26        |
| 6  | Growth and Luminescence of Polytypic InP on Epitaxial Graphene. <i>Advanced Functional Materials</i> , 2018, 28, 1705592.  | 14.9 | 17        |
| 7  | Antiresonances in the Mid-Infrared Vibrational Spectrum of Functionalized Graphene. <i>Journal of Physical Chemistry C</i> , 2017, 121, 9053-9062.   | 3.1  | 7         |
| 8  | <i>Ab initio</i> piezoelectric properties of $\text{Al}_x\text{N}_{1-x}$ : Impact of alloy configuration on the $\text{d}$ coefficient. <i>Physical Review Materials</i> , 2017, 1, .  | 2.4  | 18        |
| 9  | Optical-pump/intense-THz-probe spectroscopy of gated graphene. , 2016, , .   |      | 0         |
| 10 | Polarization-Resolved Raman Study of Bulk-like and Davydov-Induced Vibrational Modes of Exfoliated Black Phosphorus. <i>Nano Letters</i> , 2016, 16, 7761-7767.  | 9.1  | 59        |
| 11 | Surface induced magnetization reversal of MnP nanoclusters embedded in GaP. <i>Journal of Applied Physics</i> , 2016, 119, 103901.   | 2.5  | 1         |
| 12 | Intense terahertz field effects on photoexcited carrier dynamics in gated graphene. <i>Applied Physics Letters</i> , 2015, 107, .  | 3.3  | 18        |
| 13 | Tailoring the Growth Rate and Surface Facet for Synthesis of High-Quality Continuous Graphene Films from $\text{CH}_4$ at 750 °C via Chemical Vapor Deposition. <i>Journal of Physical Chemistry C</i> , 2015, 119, 11516-11523. | 3.1  | 14        |
| 14 | Direct oriented growth of armchair graphene nanoribbons on germanium. <i>Nature Communications</i> , 2015, 6, 8006.  | 12.8 | 157       |
| 15 | Impact of nucleation on step-meandering instabilities during step-flow growth on vicinal surfaces. <i>Physical Review E</i> , 2014, 89, 032406.  | 2.1  | 6         |
| 16 | Graphene CVD: Interplay Between Growth and Etching on Morphology and Stacking by Hydrogen and Oxidizing Impurities. <i>Journal of Physical Chemistry C</i> , 2014, 118, 21532-21540.   | 3.1  | 60        |
| 17 | Ferromagnetic resonance measurements of GaP epilayers with embedded MnP nanoclusters grown on GaP(001). <i>Physical Review B</i> , 2013, 87, .   | 3.2  | 13        |
| 18 | No Graphene Etching in Purified Hydrogen. <i>Journal of Physical Chemistry Letters</i> , 2013, 4, 1100-1103.   | 4.6  | 76        |

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|----|--|-----|-----------|
| 19 | Influence of statistical distributions on the electrical properties of disordered and aligned carbon nanotube networks. <i>Journal of Applied Physics</i> , 2013, 114, 114312.   | 2.5 | 21        |
| 20 | Strain and composition effects on Raman vibrational modes of silicon-germanium-tin ternary alloys. <i>Applied Physics Letters</i> , 2013, 103, .   | 3.3 | 63        |
| 21 | Thin film Ni-Si solid-state reactions: Phase formation sequence on amorphized Si. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, .   | 1.2 | 4         |
| 22 | MnP nanoclusters embedded in GaP epitaxial films grown by organometallic vapor-phase epitaxy: A reciprocal space mapping and transmission electron microscopy study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, . | 2.1 | 13        |
| 23 | Abnormal broadening of the optical transitions in (Ga,As)N/GaAs quantum wells. <i>Physical Review B</i> , 2012, 85, .  | 3.2 | 0         |
| 24 | Fano Resonances in the Midinfrared Spectra of Single-Walled Carbon Nanotubes. <i>Physical Review Letters</i> , 2012, 109, 097402.  | 7.8 | 14        |
| 25 | Temperature dependence of the photoluminescence spectra from InAs(P)/InP multilayers containing thick quantum dots: Dot-size-dependent carrier dynamics. <i>Physical Review B</i> , 2011, 83, .  | 3.2 | 8         |
| 26 | The thermally-induced reaction of thin Ni films with Si: Effect of the substrate orientation. <i>Journal of Applied Physics</i> , 2011, 110, .   | 2.5 | 35        |
| 27 | Continuum model of surface roughening and epitaxial breakdown during low-temperature Ge(001) molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011, 109, 063513.  | 2.5 | 3         |
| 28 | Modified interfacial tensions measured in situ in ternary polymer blends demonstrating partial wetting. <i>Polymer</i> , 2010, 51, 1472-1484.  | 3.8 | 23        |
| 29 | Metastable phase formation during the reaction of Ni films with Si(001): The role of texture inheritance. <i>Journal of Applied Physics</i> , 2010, 107, .   | 2.5 | 50        |
| 30 | Evidence of valence band perturbations in GaAsN/GaAs(001): Combined variable-angle spectroscopic ellipsometry and modulated photoreflectance investigation. <i>Physical Review B</i> , 2009, 80, .   | 3.2 | 11        |
| 31 | Adjusting the magnetic properties of semiconductor epilayers by the crystallographic orientation of embedded highly anisotropic magnetic nanoclusters. <i>Journal of Applied Physics</i> , 2009, 105, 07C119.  | 2.5 | 9         |
| 32 | Adhesion of Human U937 Monocytes to Nitrogen-Rich Organic Thin Films: Novel Insights into the Mechanism of Cellular Adhesion. <i>Macromolecular Bioscience</i> , 2009, 9, 911-921.   | 4.1 | 39        |
| 33 | In Situ Measure of Interfacial Tensions in Ternary and Quaternary Immiscible Polymer Blends Demonstrating Partial Wetting. <i>Macromolecules</i> , 2009, 42, 7518-7529.  | 4.8 | 49        |
| 34 | Carbon Nanotubes as Injection Electrodes for Organic Thin Film Transistors. <i>Nano Letters</i> , 2009, 9, 1457-1461.  | 9.1 | 71        |
| 35 | Chemical Characterisation of Nitrogen-Rich Plasma-Polymer Films Deposited in Dielectric Barrier Discharges at Atmospheric Pressure. <i>Plasma Processes and Polymers</i> , 2008, 5, 631-644.   | 3.0 | 78        |
| 36 | Plasma Process. <i>Polym.</i> 7/2008. <i>Plasma Processes and Polymers</i> , 2008, 5, NA-NA.   | 3.0 | 0         |

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|----|---|-----|-----------|
| 37 | GaAs <sub>1-x</sub> N <sub>x</sub> on GaAs(001): Nitrogen incorporation kinetics from trimethylgallium, tertiarybutylarsine, and 1,1-dimethylhydrazine organometallic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 2008, 310, 1040-1048. | 1.5 | 6         |
| 38 | Mechanism of the Far-Infrared Absorption of Carbon-Nanotube Films. <i>Physical Review Letters</i> , 2008, 101, 267403.  | 7.8 | 76        |
| 39 | Vacancy-mediated intermixing in InAs/InP(001) quantum dots subjected to ion implantation. <i>Journal of Applied Physics</i> , 2008, 104, 043527.  | 2.5 | 3         |
| 40 | Magnetic anisotropy in GaP(001) epilayers containing MnP nanoclusters observed by angle dependent ferromagnetic resonance measurements. <i>Journal of Applied Physics</i> , 2008, 103, 07D531.  | 2.5 | 8         |
| 41 | Low-temperature emission in dilute GaAsN alloys grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2008, 103, 063526.   | 2.5 | 7         |
| 42 | Electroluminescence from Single-Wall Carbon Nanotube Network Transistors. <i>Nano Letters</i> , 2008, 8, 2351-2355.   | 9.1 | 74        |
| 43 | Effects of grown-in defects on interdiffusion dynamics in InAs/InP(001) quantum dots subjected to rapid thermal annealing. <i>Journal of Applied Physics</i> , 2008, 103, 083526.   | 2.5 | 7         |
| 44 | Intermixing during growth of InAs self-assembled quantum dots in InP: A photoluminescence and tight-binding investigation. <i>Physical Review B</i> , 2008, 77, .   | 3.2 | 22        |
| 45 | Experimental investigation of the variation of the absorption coefficient with nitrogen content in GaAsN and GaInAsN grown on GaAs (001). <i>Journal of Applied Physics</i> , 2008, 104, 083511.  | 2.5 | 13        |
| 46 | Metal-organic vapor phase epitaxy of crystallographically oriented MnP magnetic nanoclusters embedded in GaP(001). <i>Journal of Applied Physics</i> , 2008, 104, 083501.   | 2.5 | 18        |
| 47 | Self-Organization of InAs/InP Quantum Dot Multilayers: Pseudophase Diagram Describing the Transition from Aligned to Antialigned Structures. <i>Physical Review Letters</i> , 2008, 100, 046101.  | 7.8 | 12        |
| 48 | Transport in the metallic regime of Mn-doped III-V semiconductors. <i>Physical Review B</i> , 2008, 77, .   | 3.2 | 5         |
| 49 | Magnetotransport in the insulating regime of Mn-doped GaAs. <i>Physical Review B</i> , 2008, 78, .  | 3.2 | 9         |
| 50 | Effects of long jumps, reversible aggregation, and Meyer-Neldel rule on submonolayer epitaxial growth. <i>Physical Review E</i> , 2008, 78, 021604.   | 2.1 | 4         |
| 51 | Drastic ion-implantation-induced inter-mixing during the annealing of self-assembled InAs/InP(001) quantum dots. <i>Nanotechnology</i> , 2007, 18, 015404.  | 2.6 | 11        |
| 52 | Optical emission from InAs/InP self-assembled quantum dots: evidence for As/P intermixing. <i>Semiconductor Science and Technology</i> , 2007, 22, 1282-1286.   | 2.0 | 8         |
| 53 | Compositional dependence of the elastic constants of dilute GaAs <sub>1-x</sub> N <sub>x</sub> alloys. <i>Journal of Applied Physics</i> , 2007, 101, 113507.   | 2.5 | 5         |
| 54 | Optical response of single-wall carbon nanotube sheets in the far-infrared spectral range from 1 THz to 40 THz. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 3950-3954.  | 1.5 | 18        |

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|----|--|-----|-----------|
| 55 | Carbon nanotube sheets as electrodes in organic light-emitting diodes. <i>Applied Physics Letters</i> , 2006, 88, 183104.  | 3.3 | 218       |
| 56 | Interface broadening due to ion mixing during thin film growth at the radio-frequency-biased electrode in a plasma-enhanced chemical vapor deposition environment. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 2061-2069.      | 2.1 | 8         |
| 57 | Thin film reaction of transition metals with germanium. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 474-485.   | 2.1 | 208       |
| 58 | Ion-surface interactions on c-Si(001) at the radiofrequency-powered electrode in low-pressure plasmas: Ex situ spectroscopic ellipsometry and Monte Carlo simulation study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 45-54. | 2.1 | 5         |
| 59 | Ultrafast Dynamics of Delocalized and Localized Electrons in Carbon Nanotubes. <i>Physical Review Letters</i> , 2006, 96, 027401.  | 7.8 | 39        |
| 60 | Nitrogen incorporation and lattice constant of strained dilute GaAs $_{1-x}$ N $_x$ layers on GaAs (001): An ab initio study. <i>Physical Review B</i> , 2006, 74, .   | 3.2 | 11        |
| 61 | Reaction of thin Ni films with Ge: Phase formation and texture. <i>Journal of Applied Physics</i> , 2006, 100, 034306.   | 2.5 | 62        |
| 62 | Tuning of the electronic properties of self-assembled InAs $\cdot$ InP(001) quantum dots using grown-in defect mediated intermixing. <i>Applied Physics Letters</i> , 2006, 89, 131905.  | 3.3 | 16        |
| 63 | Experimental and theoretical studies of the E $^+$ optical transition in GaAsN alloys. <i>Physical Review B</i> , 2006, 74, .  | 3.2 | 13        |
| 64 | Dynamics of ion bombardment-induced modifications of Si(001) at the radio-frequency-biased electrode in low-pressure oxygen plasmas: In situ spectroscopic ellipsometry and Monte Carlo study. <i>Journal of Applied Physics</i> , 2006, 100, 063526.                        | 2.5 | 4         |
| 65 | Atmospheric Pressure Deposition of Micropatterned Nitrogen-Rich Plasma-Polymer Films for Tissue Engineering. <i>Plasma Processes and Polymers</i> , 2005, 2, 263-270.  | 3.0 | 150       |
| 66 | Green $\hat{\epsilon}$ 's function matching method for one- and zero-dimensional heterostructures. <i>Physical Review B</i> , 2005, 72, .  | 3.2 | 0         |
| 67 | Sn-mediated Ge $\cdot$ Ge(001) growth by low-temperature molecular-beam epitaxy: Surface smoothing and enhanced epitaxial thickness. <i>Journal of Applied Physics</i> , 2005, 97, 044904.   | 2.5 | 45        |
| 68 | III-V compliant substrates implemented by nanocavities introduced by ion implantation. <i>Journal of Applied Physics</i> , 2005, 97, 064309.   | 2.5 | 2         |
| 69 | High Contrast Imaging of Interphases in Ternary Polymer Blends Using Focused Ion Beam Preparation and Atomic Force Microscopy. <i>Macromolecules</i> , 2005, 38, 2368-2375.  | 4.8 | 38        |
| 70 | Organometallic vapor phase epitaxy of GaAs $_{1-x}$ N $_x$ alloy layers on GaAs(001): Nitrogen incorporation and lattice parameter variation. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 771.                                 | 2.1 | 18        |
| 71 | Evidence for large configuration-induced band-gap fluctuations in GaAs $_{1-x}$ N $_x$ alloys. <i>Physical Review B</i> , 2004, 70, .  | 3.2 | 21        |
| 72 | Electronic and optical properties of GaAsN/GaAs quantum wells: A tight-binding study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 1606-1609.   | 2.1 | 6         |

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|----|--|-----|-----------|
| 73 | Lateral confinement and band mixing in ultrathin semiconductor quantum wells with steplike interfaces. <i>Physical Review B</i> , 2004, 70, .  | 3.2 | 8         |
| 74 | Tuning of the electronic properties of self-assembled InAs/InP(001) quantum dots by rapid thermal annealing. <i>Applied Physics Letters</i> , 2004, 84, 3382-3384.   | 3.3 | 42        |
| 75 | Characterization of GaAs <sub>1-x</sub> N <sub>x</sub> epitaxial layers by ion beam analysis. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 908.   | 2.1 | 5         |
| 76 | Study of TiO <sub>2</sub> film growth mechanisms in low-pressure plasma by in situ real-time spectroscopic ellipsometry. <i>Thin Solid Films</i> , 2004, 447-448, 40-45.   | 1.8 | 43        |
| 77 | Interface engineering during plasma-enhanced chemical vapor deposition of porous/dense SiN <sub>1.3</sub> optical multilayers. <i>Thin Solid Films</i> , 2004, 469-470, 47-53.   | 1.8 | 16        |
| 78 | Empirical tight-binding calculations of the electronic structure of dilute III-V-N semiconductor alloys. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 776.  | 2.1 | 9         |
| 79 | Lateral confinement of carriers in ultrathin semiconductor quantum wells. <i>Microelectronics Journal</i> , 2003, 34, 459-462.   | 2.0 | 2         |
| 80 | Si <sub>1-x</sub> Cy/Si(001) gas-source molecular beam epitaxy from Si <sub>2</sub> H <sub>6</sub> and CH <sub>3</sub> SiH <sub>3</sub> : Surface reaction paths and growth kinetics. <i>Journal of Applied Physics</i> , 2003, 93, 3944-3950. | 2.5 | 9         |
| 81 | Empirical tight-binding model for the electronic structure of dilute GaNAs alloys. <i>Physical Review B</i> , 2003, 67, .  | 3.2 | 45        |
| 82 | Temperature dependent contactless electroreflectance study of intersubband transitions in a self-assembled InAs/InP (001) quantum dot structure. <i>Journal of Applied Physics</i> , 2003, 94, 4995.   | 2.5 | 8         |
| 83 | Effect of steady-state hydrogen coverage on the evolution of crosshatch morphology during Si <sub>1-x</sub> Gex/Si(001) growth from hydride precursors. <i>Journal of Applied Physics</i> , 2003, 93, 1918-1925.                               | 2.5 | 16        |
| 84 | Nanocavities in He implanted InP. <i>Journal of Applied Physics</i> , 2003, 94, 6116-6121.   | 2.5 | 11        |
| 85 | Sn-enhanced epitaxial thickness during low-temperature Ge(001) molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2003, 82, 4247-4249.   | 3.3 | 11        |
| 86 | Mechanism for epitaxial breakdown during low-temperature Ge(001) molecular beam epitaxy. <i>Physical Review B</i> , 2003, 67, .  | 3.2 | 48        |
| 87 | Hydrogen-mediated quenching of strain-induced surface roughening during gas-source molecular beam epitaxy of fully-coherent Si <sub>0.7</sub> Ge <sub>0.3</sub> layers on Si(001). <i>Journal of Applied Physics</i> , 2002, 91, 3579-3588.    | 2.5 | 11        |
| 88 | Carbon incorporation pathways and lattice sites in Si <sub>1-x</sub> Cy alloys grown on Si(001) by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2002, 91, 5716-5727.  | 2.5 | 12        |
| 89 | Electronic states of ultrathin InAs/InP (001) quantum wells: A tight-binding study of the effects of band offset, strain, and intermixing. <i>Physical Review B</i> , 2002, 66, .  | 3.2 | 22        |
| 90 | C lattice site distributions in metastable Ge <sub>1-x</sub> Cy alloys grown on Ge(001) by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2002, 91, 3644-3652.  | 2.5 | 13        |

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|-----|--|-----|-----------|
| 91  | Structural properties of InAs nanocrystals formed by sequential implantation of In and As ions in the Si (100) matrix. <i>Journal of Applied Physics</i> , 2002, 92, 4664-4671.  | 2.5 | 11        |
| 92  | C incorporation and segregation during Si <sub>1-x</sub> Cy/Si() gas-source molecular beam epitaxy from Si <sub>2</sub> H <sub>6</sub> and CH <sub>3</sub> SiH <sub>3</sub> . <i>Surface Science</i> , 2002, 513, 475-484.   | 1.9 | 11        |
| 93  | Electronic structure of ScN determined using optical spectroscopy, photoemission, and ab initio calculations. <i>Physical Review B</i> , 2001, 63, .   | 3.2 | 139       |
| 94  | Epitaxial NaCl structure $\hat{\Gamma}$ -Ta <sub>Nx</sub> (001): Electronic transport properties, elastic modulus, and hardness versus N/Ta ratio. <i>Journal of Applied Physics</i> , 2001, 90, 2879-2885.  | 2.5 | 88        |
| 95  | Interfacial reaction pathways and kinetics during annealing of epitaxial Al/TiN(001) model diffusion barrier systems. <i>Thin Solid Films</i> , 2001, 391, 69-80.  | 1.8 | 19        |
| 96  | Interfacial reactions in epitaxial Al/TiN(111) model diffusion barriers: Formation of an impervious self-limited wurtzite-structure AlN(0001) blocking layer. <i>Journal of Applied Physics</i> , 2001, 89, 7841-7845.   | 2.5 | 22        |
| 97  | Synchrotron x-ray diffraction and transmission electron microscopy studies of interfacial reaction paths and kinetics during annealing of fully-002-textured Al/TiN bilayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2001, 19, 182-191. | 2.1 | 17        |
| 98  | Interfacial reaction pathways and kinetics during annealing of 111-textured Al/TiN bilayers: A synchrotron x-ray diffraction and transmission electron microscopy study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2001, 19, 2207-2216.    | 2.1 | 12        |
| 99  | Ultra-highly doped Si <sub>1-x</sub> Gex(001):B gas-source molecular-beam epitaxy: Boron surface segregation and its effect on film growth kinetics. <i>Journal of Applied Physics</i> , 2001, 89, 194-205.  | 2.5 | 8         |
| 100 | Quantitative C lattice site distributions in epitaxial Ge <sub>1-x</sub> Cy/Ge(001) layers. <i>Journal of Applied Physics</i> , 2001, 90, 3910-3918.   | 2.5 | 13        |
| 101 | Temperature-modulated Si(001):As gas-source molecular beam epitaxy: Growth kinetics and As incorporation. <i>Applied Physics Letters</i> , 2001, 79, 3263-3265.  | 3.3 | 2         |
| 102 | Si(011)16Å-2 gas-source molecular beam epitaxy: Growth kinetics. <i>Applied Physics Letters</i> , 2000, 76, 2853-2855.   | 3.3 | 8         |
| 103 | Ultrahigh B doping (<math>\sim 10^{22} \text{cm}^{-3}</math>) during Si(001) gas-source molecular-beam epitaxy: B incorporation, electrical activation, and hole transport. <i>Physical Review B</i> , 2000, 61, 7628-7644.  | 3.2 | 34        |
| 104 | Epitaxial metastable Ge <sub>1-x</sub> Cy (<math>y \approx 0.02</math>) alloys grown on Ge(001) from hyperthermal beams: C incorporation and lattice sites. <i>Journal of Applied Physics</i> , 2000, 88, 96-104.  | 2.5 | 8         |
| 105 | Arsenic incorporation during Si(001):As gas-source molecular-beam epitaxy from Si <sub>2</sub> H <sub>6</sub> and AsH <sub>3</sub> : Effects on film-growth kinetics. <i>Journal of Applied Physics</i> , 2000, 88, 7067-7078.   | 2.5 | 13        |
| 106 | Role of fast sputtered particles during sputter deposition: Growth of epitaxial Ge <sub>0.99</sub> C <sub>0.01</sub> /Ge(001). <i>Physical Review B</i> , 2000, 62, 11203-11208.   | 3.2 | 9         |
| 107 | Arsenic-doped Si(001) gas-source molecular-beam epitaxy: Growth kinetics and transport properties. <i>Applied Physics Letters</i> , 1999, 74, 1290-1292.   | 3.3 | 7         |
| 108 | Hybrid surface roughening modes during low-temperature heteroepitaxy: Growth of fully-strained metastable Ge <sub>1-x</sub> Snx alloys on Ge(001)2Å-1. <i>Physical Review B</i> , 1999, 60, 15993-15998.   | 3.2 | 15        |

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|-----|---|-----|-----------|
| 109 | Growth of $\text{Si}_{1-x}\text{Ge}_x(011)$ on $\text{Si}(011)16\text{\AA}-2$ by gas-source molecular beam epitaxy: Growth kinetics, Ge incorporation, and surface phase transitions. <i>Journal of Applied Physics</i> , 1999, 85, 501-511.                    | 2.5 | 11        |
| 110 | Microstructural evolution and Poisson ratio of epitaxial ScN grown on $\text{TiN}(001)/\text{MgO}(001)$ by ultrahigh vacuum reactive magnetron sputter deposition. <i>Journal of Applied Physics</i> , 1999, 86, 5524-5529.                                     | 2.5 | 68        |
| 111 | Low-temperature growth and critical epitaxial thicknesses of fully strained metastable $\text{Ge}_{1-x}\text{Sn}_x$ ( $x \approx 0.26$ ) alloys on $\text{Ge}(001)2\text{\AA}-1$ . <i>Journal of Applied Physics</i> , 1998, 83, 162-170.                       | 2.5 | 124       |
| 112 | Raman scattering from fully strained $\text{Ge}_{1-x}\text{Sn}_x$ ( $x \approx 0.22$ ) alloys grown on $\text{Ge}(001)2\text{\AA}-1$ by low-temperature molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1998, 84, 2219-2223.                        | 2.5 | 40        |
| 113 | Pathways for hydrogen desorption from $\text{Si}_{1-x}\text{Ge}_x(001)$ during gas-source molecular-beam epitaxy and ultrahigh-vacuum chemical vapor deposition. <i>Physical Review B</i> , 1998, 58, 4803-4808.  | 3.2 | 30        |
| 114 | Toward quantum dot laser diodes emitting at $1.5 \mu\text{m}$ . , 1998, 3491, 271.  |     | 5         |
| 115 | Metalorganic vapor phase epitaxy of coherent self-assembled InAs nanometer-sized islands in $\text{InP}(001)$ . <i>Applied Physics Letters</i> , 1997, 71, 527-529.   | 3.3 | 97        |
| 116 | Strain and relaxation effects in $\text{InAsP}/\text{InP}$ multiple quantum well optical modulator devices grown by metal-organic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 1997, 81, 1905-1915.   | 2.5 | 17        |
| 117 | Microstructure and strain relaxation in organometallic vapor phase epitaxy of strain-compensated $\text{GaInP}/\text{InAsP}$ multilayers on $\text{InP}(001)$ . <i>Journal of Applied Physics</i> , 1997, 81, 3501-3511.  | 2.5 | 10        |
| 118 | Metalorganic vapor phase epitaxial growth and structural characterization of self-assembled InAs nanometer-sized Islands on $\text{InP}(001)$ . <i>Journal of Electronic Materials</i> , 1997, 26, 1205-1213.   | 2.2 | 7         |
| 119 | In situ scanning tunneling microscopy studies of the evolution of surface morphology and microstructure in epitaxial $\text{TiN}(001)$ grown by ultra-high-vacuum reactive magnetron sputtering. <i>Surface and Coatings Technology</i> , 1997, 94-95, 403-408. | 4.8 | 31        |
| 120 | Step-flow epitaxial growth on two-domain surfaces. <i>Journal of Applied Physics</i> , 1996, 79, 1423-1434.   | 2.5 | 9         |
| 121 | Self-consistent determination of the band offsets in $\text{InAsP}_{1-x}/\text{InP}$ strained-layer quantum wells and the bowing parameter of bulk $\text{InAsP}_{1-x}$ . <i>Physical Review B</i> , 1996, 53, 1990-1996.                                       | 3.2 | 53        |